

## Black Plastic Photodiode

LTR-516AB/LTR-526AB/LTR-536AB/LTR-546AB

### Features

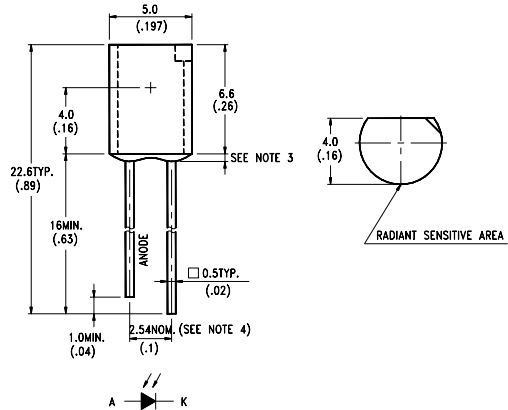
- High photo sensitivity.
- Suitable for infrared radiation.
- Low junction capacitance.
- High cut-off frequency.
- Fast switching time.

### Description

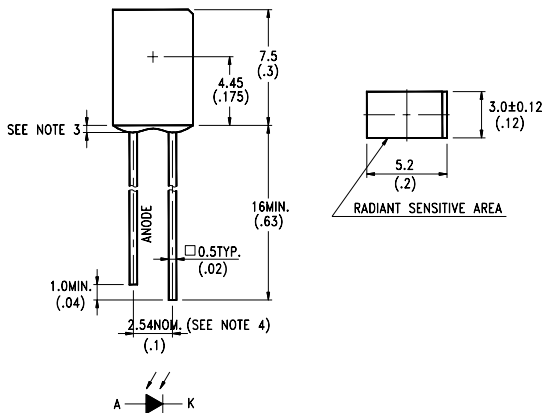
The LTR-516AB/LTR-526AB/LTR-536AB/LTR-546AB are special dark plastic package that cut the visible light and suitable for the detectors of infrared applications. This series is spectrally matched to the LTE-3677/LTE-3376 of infrared emitting diodes.

### Package Dimensions

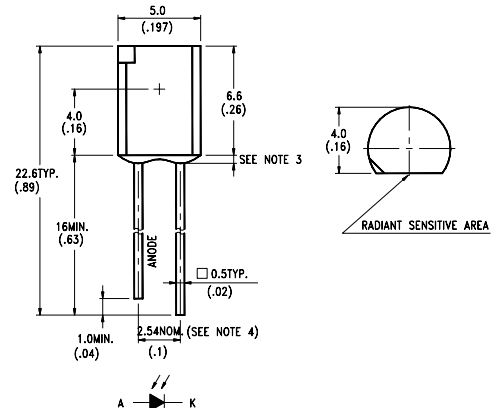
LTR-516AB



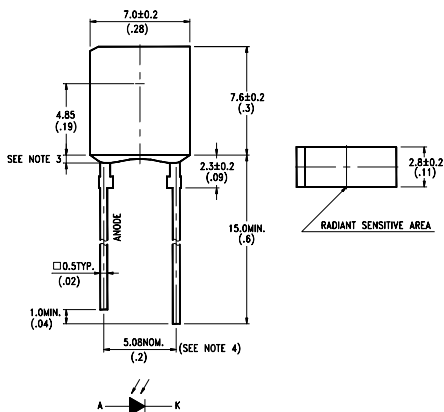
LTR-536AB



LTR-526AB



LTR-546AB



### Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is  $\pm 0.25\text{mm}$  (.010") unless otherwise noted.
3. Protruded resin under flange is 1.5mm (.059") max.
4. Lead spacing is measured where the leads emerge from the package.
5. Specifications are subject to change without notice.

## Absolute Maximum Ratings at Ta=25°C

| Parameter  | Maximum Rating      | Unit |
|--|---------------------|------|
| Power Dissipation  | 150                 | mW   |
| Reverse Break Down Voltage                                 | 30                  | V    |
| Operating Temperature Range                                | -40°C to +85°C      |      |
| Storage Temperature Range                                  | -55°C to +100°C     |      |
| Lead Soldering Temperature<br>[1.6mm (.063 in.) from body] | 260°C for 5 Seconds |      |

## Electrical Optical Characteristics at Ta=25°C

| Parameter                         | Symbol           | Min. | Typ. | Max. | Unit    | Test Condition                                    |
|-----------------------------------|------------------|------|------|------|---------|---|
| Reverse Break Down Voltage        | $V_{(BR)R}$      | 30   |      |      | V       | $I_R=100 \mu A$<br>$E_e=0mW/cm^2$                 |
| Reverse Dark Current              | $I_{D(R)}$       |      |      | 30   | nA      | $V_R=10V$<br>$E_e=0mW/cm^2$                       |
| Open Circuit Voltage              | $V_{OC}$         |      | 350  |      | mV      | $\lambda = 940nm$<br>$E_e=0.5mW/cm^2$             |
| Rise Time                         | $T_r$            |      | 50   |      | nsec    | $V_R=10V$<br>$\lambda = 940nm$<br>$R_L=1K \Omega$ |
| Fall Time                         | $T_f$            |      | 50   |      | nsec    |   |
| Light Current                     | $I_s$            | 1.7  | 2    |      | $\mu A$ | $V_R=5V$<br>$\lambda = 940nm$<br>$E_e=0.1mW/cm^2$ |
| Total Capacitance                 | $C_T$            |      | 25   |      | pF      | $R=3V$<br>$V_F=1MHz$<br>$E_e=0mW/cm^2$            |
| Wavelength of the Max Sensitivity | $\lambda_{SMAX}$ |      | 900  |      | nm      |   |

## Typical Electrical/Optical Characteristic Curves (25°C Ambient Temperature Unless Otherwise Noted)

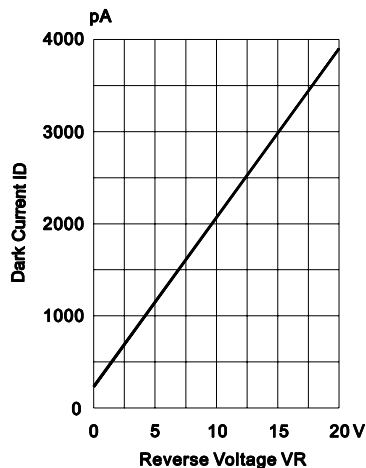


Fig.1 DARK CURRENT VS.  
REVERSE VOLTAGE  
TA=25 XC, Ee=0 mW/cm<sup>2</sup>

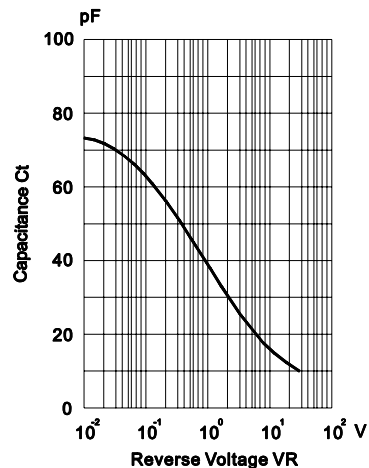


Fig.2 CAPACITANCE VS.  
REVERSE VOLTAGE  
F=1MHZ; Ee=0mW/cm<sup>2</sup>

# Typical Electrical/Optical Characteristic Curves (25°C Ambient Temperature Unless Otherwise Noted)

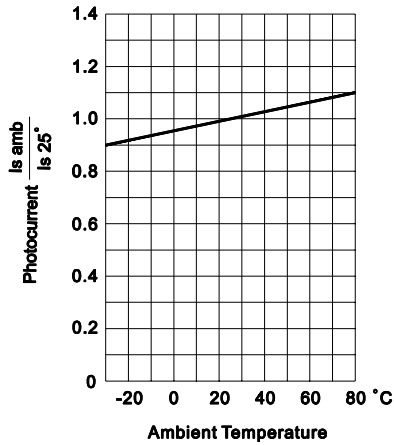


Fig.3 PHOTOCURRENT VS. AMBIENT TEMPERATURE

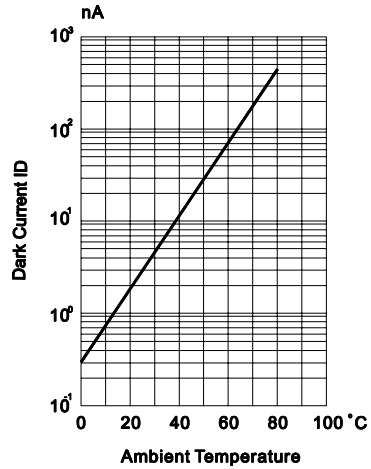


Fig.4 DARK CURRENT AMBIENT TEMPERATURE  
VR=10, Ee=0mW/cm<sup>2</sup>

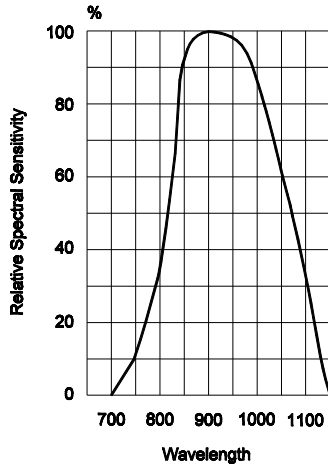


Fig.5 RELATIVE SPECTRAL SENSITIVITY VS WAVELENGTH

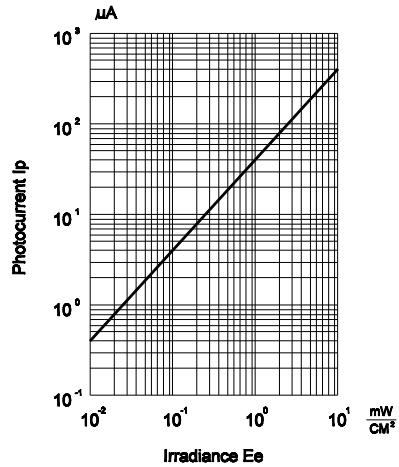


Fig.6 PHOTOCURRENT VS IRRADIANCE λ= 940 nm

# Typical Electrical/Optical Characteristic Curves (25°C Ambient Temperature Unless Otherwise Noted)

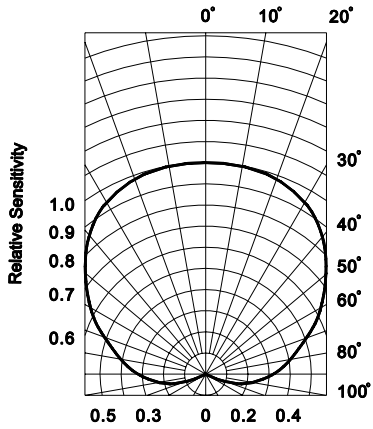


Fig.7 SENSITIVITY DIAGRAM

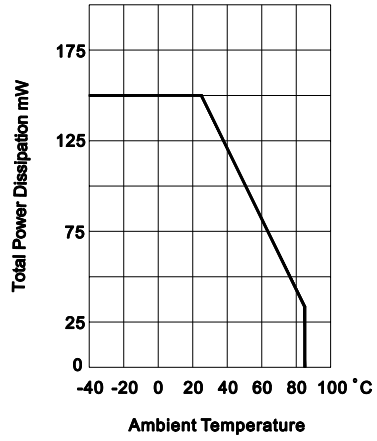


Fig.8 TOTAL POWER DISSIPATION VS  
AMBIENT TEMPERATURE